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# FDMC8554 N-Channel Power Trench<sup>®</sup> MOSFET

20V, 16.5A, 5mΩ

## Features

- Max  $r_{DS(on)}$  = 5mΩ at  $V_{GS} = 10V$ ,  $I_D = 16.5A$
- Max  $r_{DS(on)}$  = 6.4mΩ at  $V_{GS} = 4.5V$ ,  $I_D = 14A$
- Low Profile - 1mm max in Power 33
- RoHS Compliant

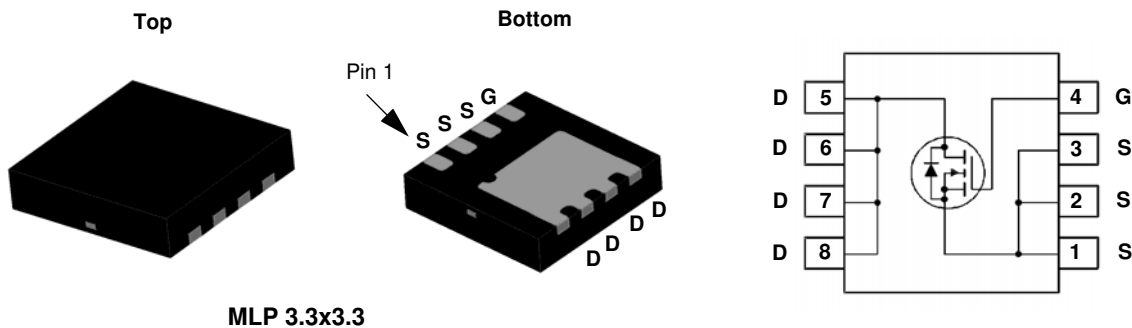


## General Description

This N-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced Power Trench process. It has been optimized for power management applications.

## Application

- DC - DC Conversion



## MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter  | Rated       | Units            |
|----------------|--|-------------|------------------|
| $V_{DS}$       | Drain to Source Voltage                              | 20          | V                |
| $V_{GS}$       | Gate to Source Voltage                               | $\pm 20$    | V                |
| $I_D$          | Drain Current -Continuous $T_C = 25^\circ\text{C}$   | 16.5        | A                |
|                | -Continuous $T_A = 25^\circ\text{C}$ (Note 1a)       | 16.5        |                  |
|                | -Pulsed  | 36          |                  |
| $P_D$          | Power Dissipation $T_C = 25^\circ\text{C}$           | 41          | W                |
|                | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) | 2.0         |                  |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range     | -55 to +150 | $^\circ\text{C}$ |

## Thermal Characteristics

|                 |   |    |                    |
|-----------------|---|----|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case              | 3  | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 60 |                    |

## Package Marking and Ordering Information

| Device Marking | Device   | Package  | Reel Size | Tape Width | Quantity   |
|----------------|----------|----------|-----------|------------|------------|
| FDMC8554       | FDMC8554 | Power 33 | 7"        | 8mm        | 3000 units |

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

### Off Characteristics

|                                      |   |  |    |      |           |                      |
|--------------------------------------|---|--|----|------|-----------|----------------------|
| $BV_{DSS}$                           | Drain to Source Breakdown Voltage         | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$                         | 20 |      |           | V                    |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$          |    | 15.7 |           | mV/ $^\circ\text{C}$ |
| $I_{DSS}$                            | Zero Gate Voltage Drain Current           | $V_{DS} = 16\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$ |    |      | 1         | $\mu\text{A}$        |
| $I_{GSS}$                            | Gate to Source Leakage Current            | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$                      |    |      | $\pm 100$ | nA                   |

### On Characteristics

|  |  |  |     |      |     |                      |
|--|--|--|-----|------|-----|----------------------|
| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                         | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$                            | 1.0 | 1.8  | 3.0 | V                    |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$          |     | -6.1 |     | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$                           | Drain to Source On Resistance                            | $V_{GS} = 10\text{V}, I_D = 16.5\text{A}$                          |     | 3.6  | 5.0 | m $\Omega$           |
|  |  | $V_{GS} = 4.5\text{V}, I_D = 14\text{A}$                           |     | 4.6  | 6.4 |                      |
|  |  | $V_{GS} = 10\text{V}, I_D = 16.5\text{A}, T_J = 125^\circ\text{C}$ |     | 5.4  | 7.1 |                      |
| $g_{FS}$                               | Forward Transconductance                                 | $V_{DS} = 5\text{V}, I_D = 16.5\text{A}$                           |     | 62   |     | S                    |

### Dynamic Characteristics

|           |                              |  |                   |      |      |    |
|-----------|------------------------------|--|-------------------|------|------|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ |                   | 2540 | 3380 | pF |
| $C_{oss}$ | Output Capacitance           |  |                   | 795  | 1060 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |  |                   | 510  | 765  | pF |
| $R_g$     | Gate Resistance              |  | $f = 1\text{MHz}$ |      | 1.2  |    |

### Switching Characteristics

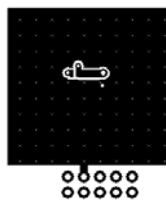
|              |                               |   |  |     |    |    |
|--------------|-------------------------------|---|--|-----|----|----|
| $t_{d(on)}$  | Turn-On Delay Time            | $V_{DD} = 10\text{V}, I_D = 16.5\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$ |  | 13  | 24 | ns |
| $t_r$        | Rise Time                     |   |  | 10  | 20 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time           |   |  | 32  | 51 | ns |
| $t_f$        | Fall Time                     |   |  | 7   | 14 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V      | $V_{DD} = 10\text{V}, I_D = 16.5\text{A}$   |  | 44  | 62 | nC |
| $Q_{g(TOT)}$ | Total Gate Charge at 4.5V     |   |  | 24  | 34 | nC |
| $Q_{gs}$     | Gate to Source Gate Charge    |   |  | 8.5 |    | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |   |  | 10  |    | nC |

### Drain-Source Diode Characteristics

|          |                                       |   |  |     |     |    |
|----------|---------------------------------------|---|--|-----|-----|----|
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = 16.5\text{A}$ (Note 2)     |  | 0.8 | 1.3 | V  |
| $t_{rr}$ | Reverse Recovery Time                 | $I_F = 16.5\text{A}, di/dt = 100\text{A}/\mu\text{s}$ |  | 31  | 47  | ns |
| $Q_{rr}$ | Reverse Recovery Charge               |   |  | 22  | 33  | nC |

#### Notes:

1:  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



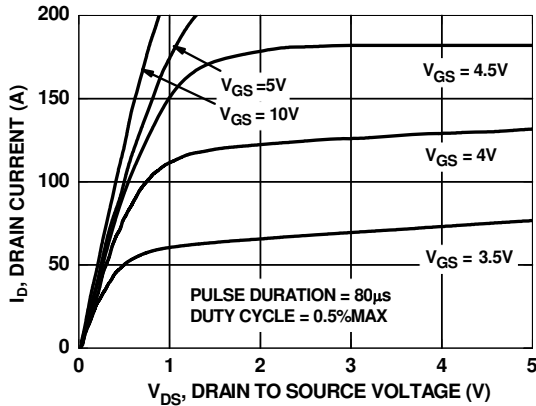
a.  $60^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper



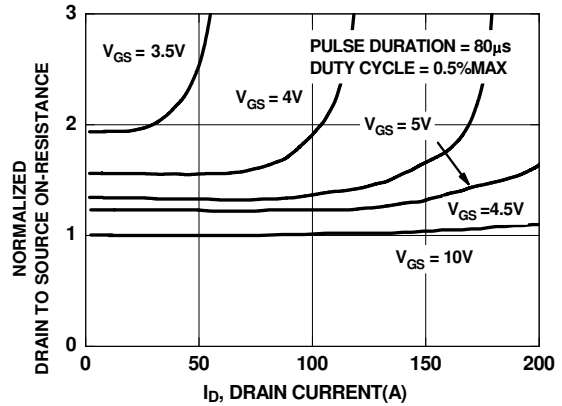
b.  $135^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

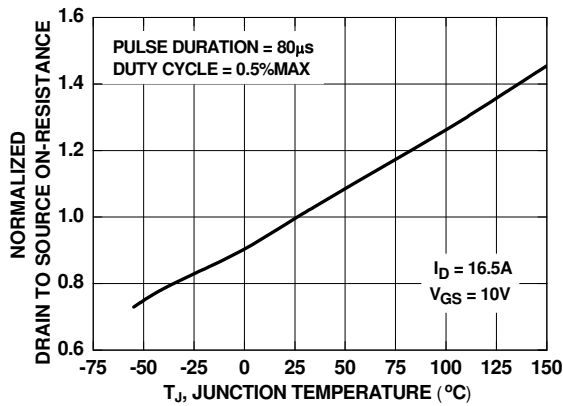
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



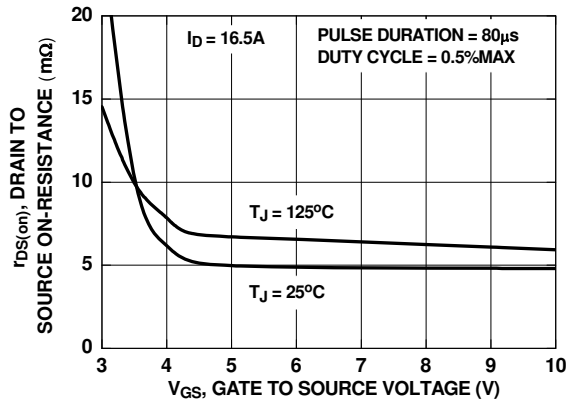
**Figure 1. On-Region Characteristics**



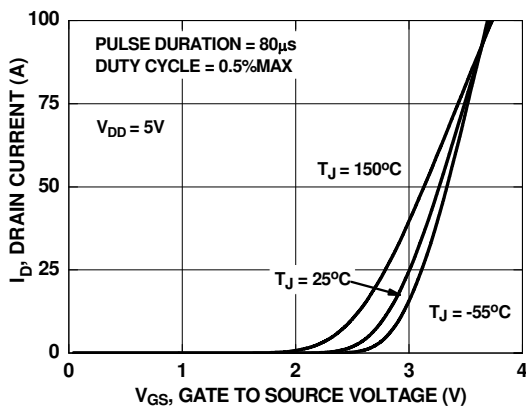
**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**



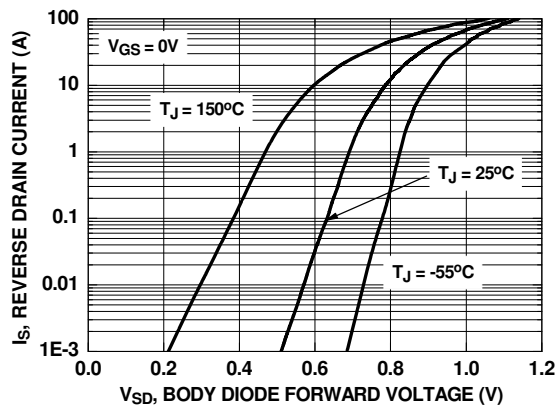
**Figure 3. Normalized On-Resistance vs Junction Temperature**



**Figure 4. On-Resistance vs Gate to Source Voltage**

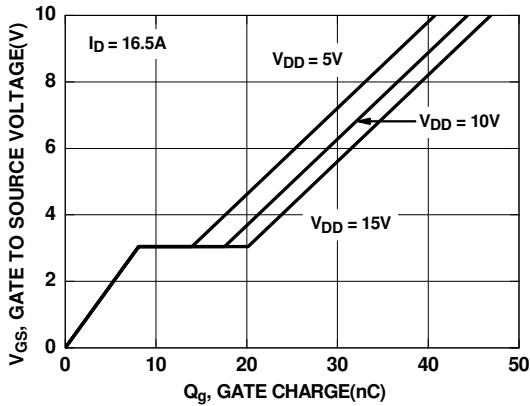


**Figure 5. Transfer Characteristics**

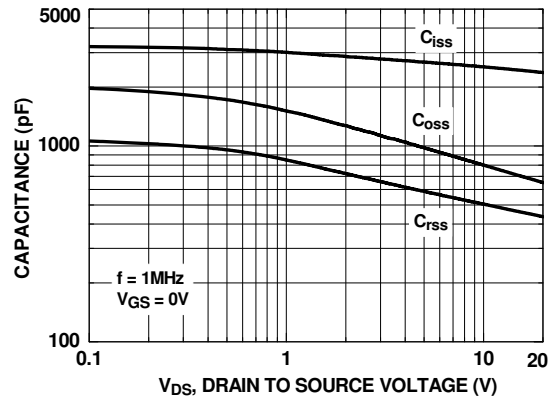


**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

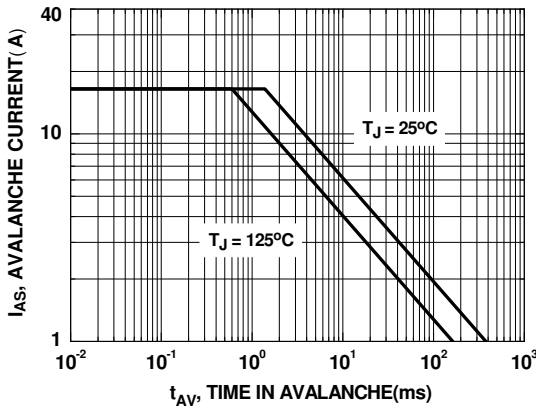
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



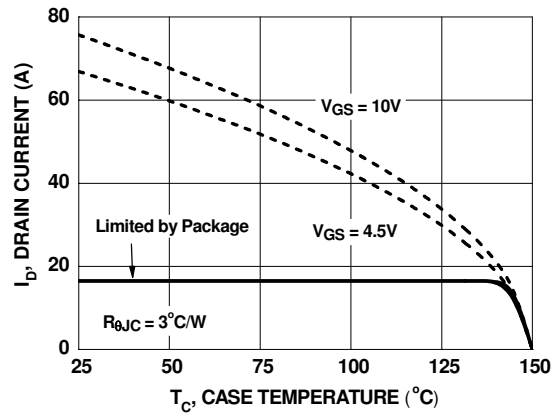
**Figure 7. Gate Charge Characteristics**



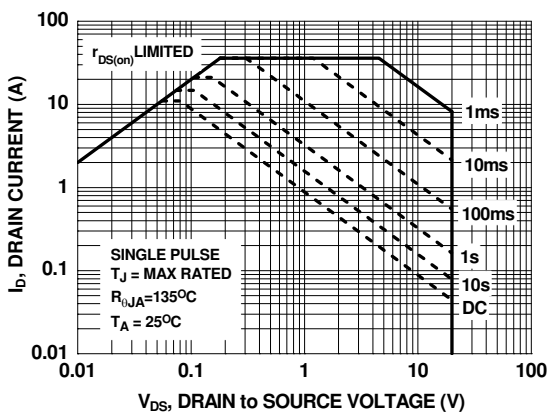
**Figure 8. Capacitance vs Drain to Source Voltage**



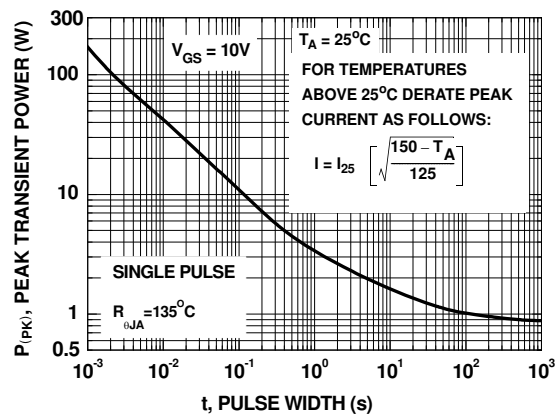
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Ambient Temperature**

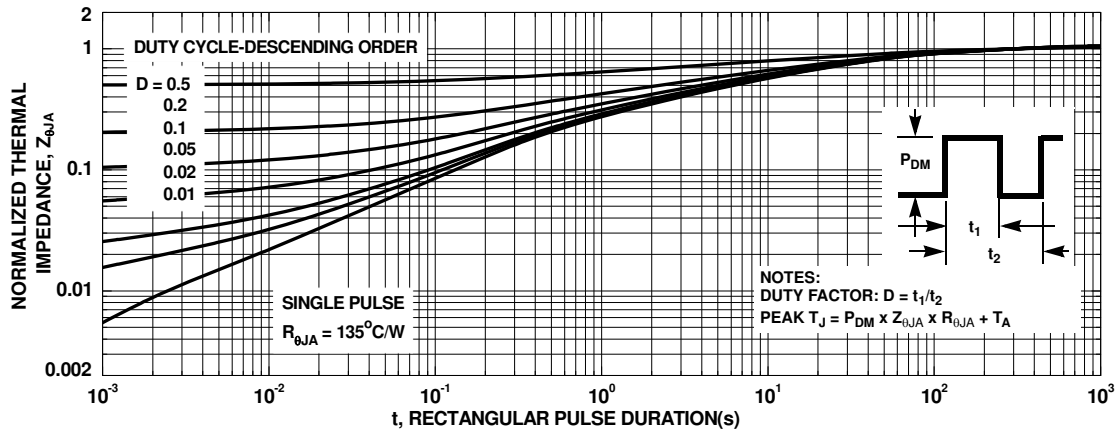


**Figure 11. Forward Bias Safe Operating Area**



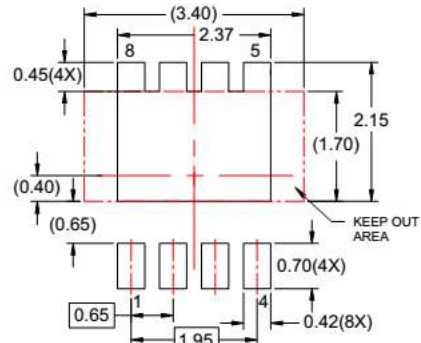
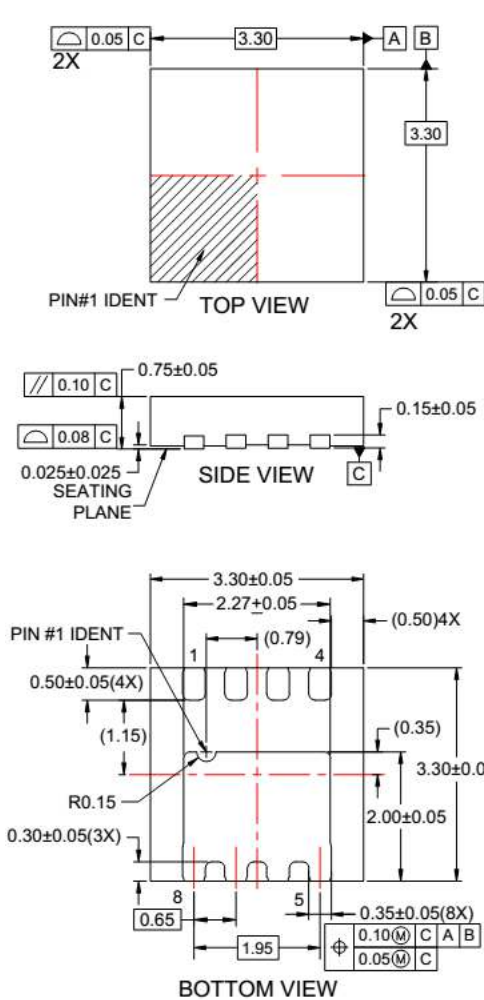
**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 13. Transient Thermal Response Curve**

## Dimensional Outline and Pad Layout



RECOMMENDED LAND PATTERN

### NOTES:

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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
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- E. DRAWING FILENAME: MKT-MLP08Rev3.







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